

L Number	Hits	Search Text	DB	Time stamp
1	4	((("6160268") or ("6197624"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 08:53
2	13	"1174535"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 08:54
6	1	"200286423"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 08:55
7	2	"2000286423"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 08:56
10	25	"0088504"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 09:00
11	0	"20010068784"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 08:59
12	0	"1020010068784"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 08:59
13	0	"10-2001-0068784"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 09:00
14	3	'KR' and '0088504'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 09:00
15	139	'bottom gate thin film transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 09:02
16	4	'bottom gate thin film transistor' and 'Sanyo'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 09:03
17	1	JP2000338708	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 09:04
25	897	@ad<=20001107 and yamazaki-shunpei.in. and 'TFT'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 09:53
27	3	@ad<=20001107 and yamazaki-shunpei.in. and semiconductor-energy-laboratory.as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 09:44

30	155	@ad<=20001107 and yamazaki-shunpei.in. and 'TFT' and 'bottom gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 09:54
32	701	@ad<=20001107 and 'inverted transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 11:01
-	36	@ad<=20001107 and 'thin film transistor' and 'selective' near 'doping'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 08:51
-	2	@ad<=20001107 and 'thin film transistor' and 'cleaning' near 'native oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/16 14:53
-	1	@ad<=20001107 and 'TFT' and 'cleaning' near 'native oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/16 14:53
-	18	@ad<=20001107 and 'TFT' and 'remove' near 'native oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 16:10
-	7	@ad<=20001107 and 'TFT' and 'removal' near 'native oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/16 15:06
-	590	@ad<=20001107 and "thin film transistor" and "ohmic contact layer"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/16 15:26
-	60	@ad<=20001107 and "thin film transistor" and "remove" near 'oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/17 08:43
-	1	"3859716".PN.	USPAT	2002/07/16 17:05
-	1	"4757026".PN.	USPAT	2002/07/16 17:05
-	1	"4876213".PN.	USPAT	2002/07/16 17:05
-	1	"5182620".PN.	USPAT	2002/07/16 17:06
-	1	"5266823".PN.	USPAT	2002/07/16 17:06
-	1	"5323042".PN.	USPAT	2002/07/16 17:06
-	1	"5998841".PN.	USPAT	2002/07/16 17:06
-	1	"5962872".PN.	USPAT	2002/07/16 17:06
-	1	"5939731".PN.	USPAT	2002/07/16 17:07
-	1	"5804471".PN.	USPAT	2002/07/16 17:07
-	1	"5856689".PN.	USPAT	2002/07/16 17:08
-	1	"5804471".PN.	USPAT	2002/07/16 17:08

-	3055	((438/149) or (438/158) or (438/315) or (438/334)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 07:41
-	6	((438/149) or (438/158) or (438/315) or (438/334)).CCLS.) and @ad<=20001107 and "thin film transistor" and "remove" near 'oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/07 13:51
-	608	((438/149) or (438/158) or (438/315) or (438/334)).CCLS.) and @ad<=20001107 and "thin film transistor"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/17 08:46
-	5525	((438/149) or (438/158-159) or (438/315) or (438/334) or (438/163) or (438/166) or (257/69) or (257/72) or (257/59)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:43
-	16	((438/149) or (438/158-159) or (438/315) or (438/334) or (438/163) or (438/166) or (257/69) or (257/72) or (257/59)).CCLS.) and @ad<=20001107 and "thin film transistor" and "remove" near 'oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 07:43
-	1	@ad<=20001107 and 'thin film transistor' and 'burried gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:56
-	30430	@ad<=20001107 and 'thin film transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:59
-	779	(@ad<=20001107 and 'thin film transistor') and short same channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 16:01
-	719	(@ad<=20001107 and 'thin film transistor') and short same channel and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 16:02
-	18	@ad<=20001107 and 'TFT' and 'remove' near 'native oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 08:50
-	1	"5641974".PN.	USPAT	2002/12/17 16:13
-	1	"5780871".PN.	USPAT	2002/12/17 16:13
-	1	"5837619".PN.	USPAT	2002/12/17 16:14
-	1	"5882165".PN.	USPAT	2002/12/17 16:14
-	1	"5917571".PN.	USPAT	2002/12/17 16:14
-	1	"6177302".PN.	USPAT	2002/12/17 16:14
-	4767	((257/59) or (257/61) or (257/72) or (257/347) or (349/42-43)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 07:41
-	114	@ad<=20001107 and 'bottom gate TFT'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 07:45

-	2	("6107641").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/07 14:05
-	3424	((438/149) or (438/158) or (438/315) or (438/334)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 07:42
-	5311	((257/59) or (257/61) or (257/72) or (257/347) or (349/42-43)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 07:44
-	16	((438/149) or (438/158-159) or (438/315) or (438/334) or (438/163) or (438/166) or (257/69) or (257/72) or (257/59)).CCLS.) and @ad<=20001107 and 'thin film transistor' and 'remove' near 'oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/08 07:44
-	493	@ad<=20001107 and 'bottom gate' with 'TFT'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 09:02
-	2	"20020090774"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 14:41
-	1	"5712191".PN.	USPAT	2004/06/10 14:59
-	545	@ad<=20001107 and 'bottom gate' with 'TFT'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/18 10:56